

MJE13003

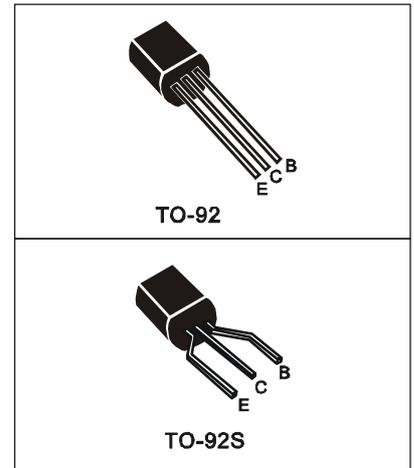
NPN EPITAXIAL PLANAR TRANSISTOR

Description

The MJE13003 is designed for high voltage. High speed switching inductive circuits and amplifier applications.

Features

- High Speed Switching
- Low Saturation Voltage
- High Reliability



Absolute Maximum Ratings (Ta=25°C)

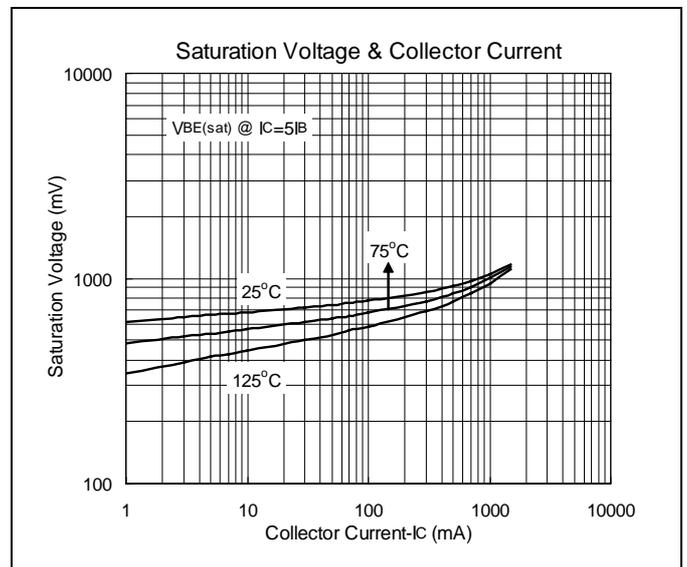
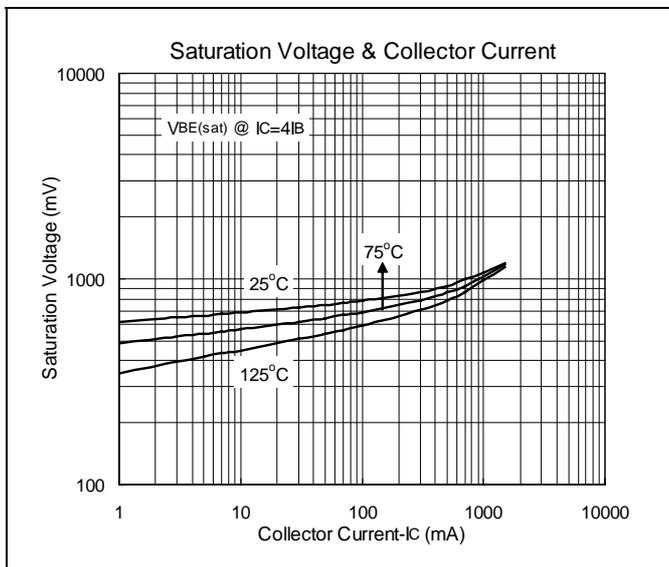
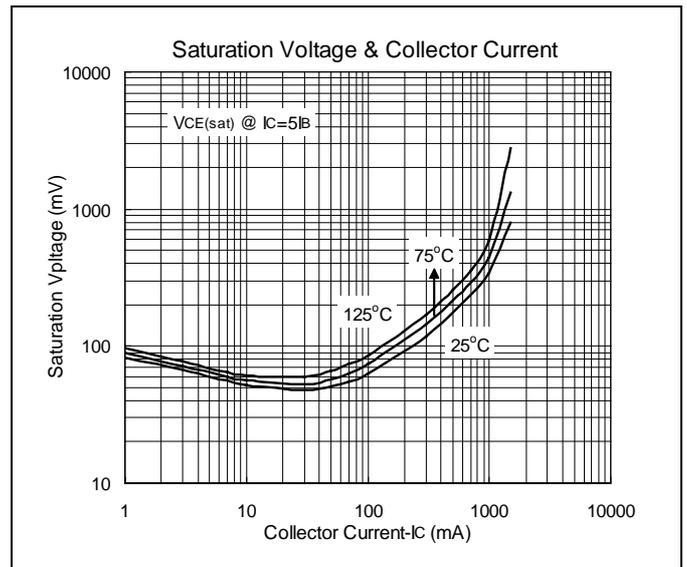
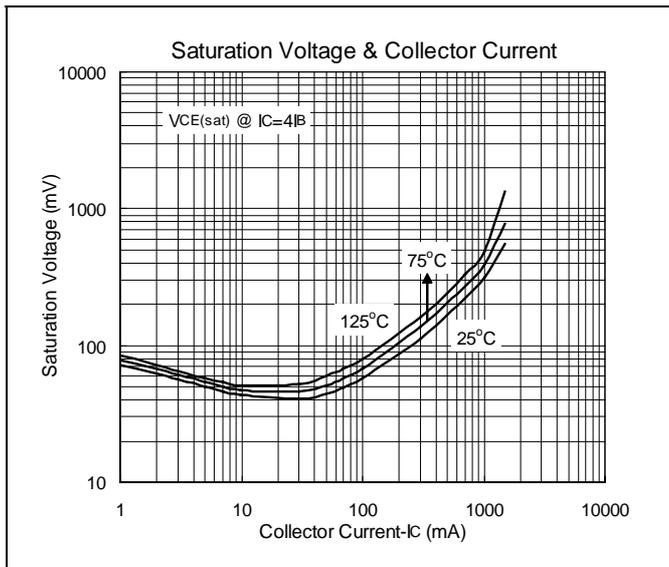
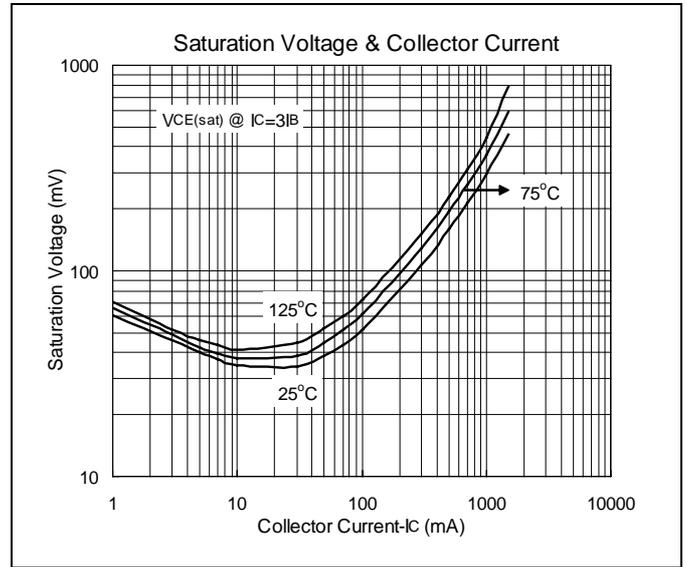
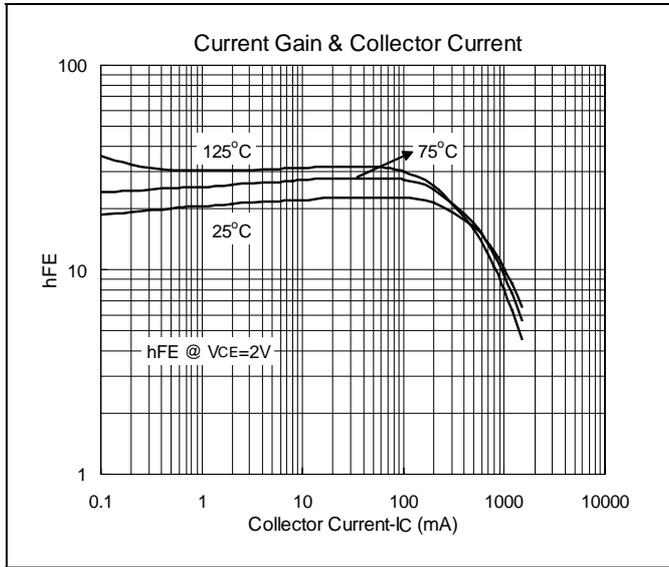
- Maximum Temperatures
 - Storage Temperature -50 ~ +150 °C
 - Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
 - Total Power Dissipation (Ta=25°C) 3.5 W
 - Total Power Dissipation (Tc=25°C) 30 W
- Maximum Voltages and Currents
 - BVCBO Collector to Base Voltage 600 V
 - BVCEO Collector to Emitter Voltage 400 V
 - BVEBO Emitter to Base Voltage 8 V
 - IC Collector Current (DC) 1 A
 - IC Collector Current (Pulse) 2 A

Characteristics (Ta=25°C)

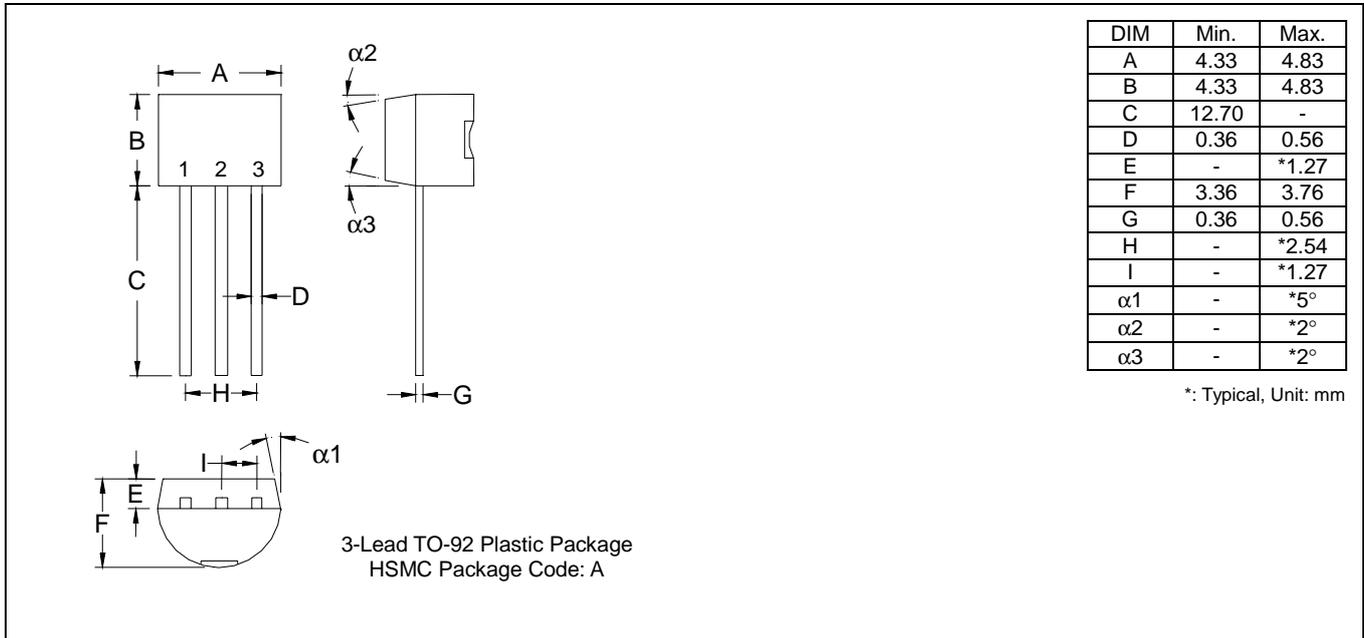
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	600	-	-	V	IC=1mA, IE=0
BVCEO	400	-	-	V	IC=10mA, IB=0
BVEBO	8	-	-	V	IE=1mA, IC=0
ICBO	-	-	10	uA	VCB=600V, IE=0
IEBO	-	-	10	uA	VBE=9V, IC=0
*VCE(sat)1	-	-	0.8	V	IC=0.1A, IB=10mA
*VCE(sat)2	-	-	0.9	V	IC=0.3A, IB=30mA
*VBE(sat)1	-	-	1.2	V	IC=0.1A, IB=10mA
*VBE(sat)2	-	-	1.8	V	IC=0.3A, IB=30mA
*hFE1	10	-	50		IC=0.3A, VCE=5V
*hFE2	10	-	-		IC=0.5A, VCE=5V
*hFE3	6	-	-		IC=1A, VCE=5V

*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%

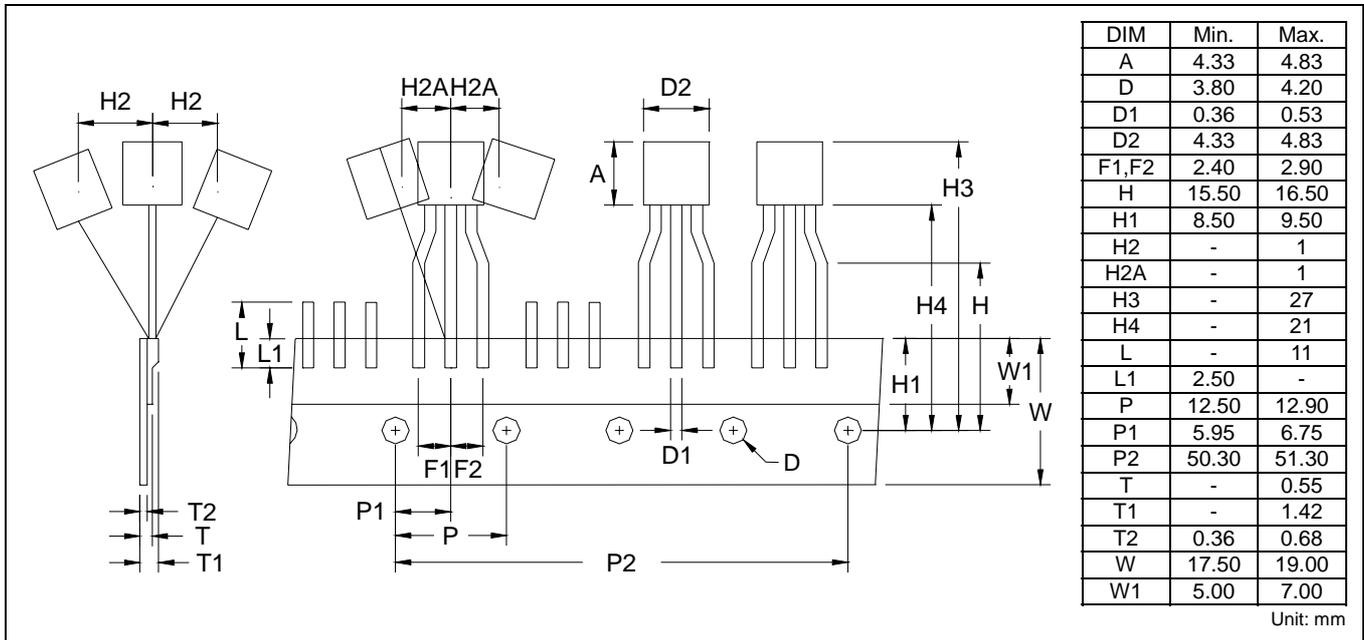
Characteristics Curve



TO-92 Dimension



TO-92 Taping Dimension



Head Office And Factory:

• Head Office

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